

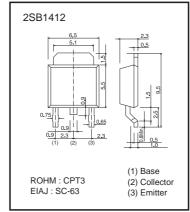
Low frequency transistor (-20V,-5A) ^{25B1412}

- •Features 1) Low VCE(sat).
- $V_{CE(sat)} = -0.35V (Typ.)$
- (Ic/IB = -4A / -0.1A)
- 2) Excellent DC current gain characteristics.
- 3) Complements the 2SD2118.

Structure

Epitaxial planar type PNP silicon transistor

•Dimensions (Unit : mm)



* Denotes hre

Absolute max	kimum rat	t ings (Ta=25°	°C)		
Parameter		Symbol	Limits	Unit	
Collector-base voltage		Vсво	-30	V	
Collector-emitter voltage		Vceo	-20	V	
Emitter-base voltage		Vebo	-6	V	
0.11			-5	A(DC)	
Collector current		lc0	-10	A(Pulse) *1	
Collector power	00004440	B1412 Pc 1 10	1	W	
dissipation	25B1412		W(Tc=25°C)		
Junction temperature		Tj	150	°C	
Storage tempera	Storage temperature		–55 to 150	°C	

*1 Single pulse, Pw=10ms

•Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Collector-base breakdown voltage	ВУсво	-30	-	-	V	Ic=-50μA
Collector-emitter breakdown voltage	BVCEO	-20	-	-	V	Ic=-1mA
Emitter-base breakdown voltage	ВУево	-6	-	-	V	Iε=-50μA
Collector cutoff current	Ісво	-	-	-0.5	μΑ	Vcb=-20V
Emitter cutoff current	Іево	-	-	-0.5	μΑ	Veb=-5V
Collector-emitter saturation voltage	VCE(sat)	-	0.35	-1.0	V	Ic/I _B = -4A/ -0.1A *
DC current transfer ratio	hfe	82	-	390	_	Vce= -2V, Ic= -0.5A *
Transition frequency	f⊤	-	120	-	MHz	Vce= –6V, Ie=50mA, f=100MHz
Output capacitance	Cob	-	60	-	pF	Vcb=-20V, Ie=0A, f=1MHz

* Measured using pulse current.

Packaging specifications and hre

		Package	Taping
		Code	TL
Туре	hfe	Basic ordering unit (pieces)	2500
2SB1412	PQR		0

hFE values are classified as follows :

Item	Р	Q	R
hfe	82 to 180	120 to 270	180 to 390

•Electrical characteristic curves

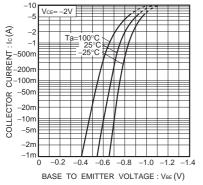


Fig.1 Grounded emitter propagation characteristics

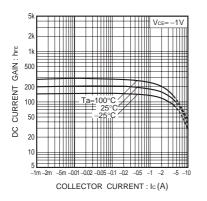


Fig.4 DC current gain vs. collector current (II)

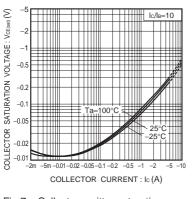
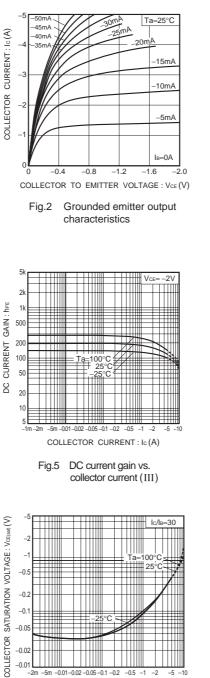
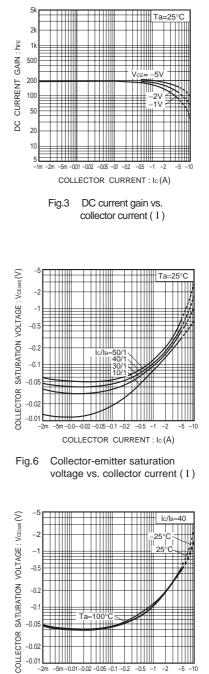


Fig.7 Collector-emitter saturation voltage vs. collector current (II)



COLLECTOR CURRENT : Ic (A)

Fig.8 Collector-emitter saturation voltage vs. collector current (III)



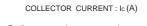
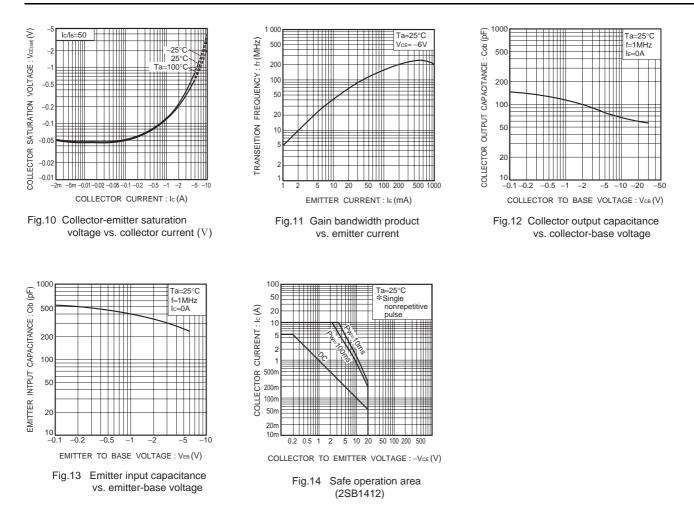


Fig.9 Collector-emitter saturation voltage vs. collector current (IV)



	Notes
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